

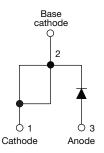
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Vishay Semiconductors

HEXFRED®, Ultrafast Soft Recovery Diode, 6 A



TO-247AC modified



PRODUCT SUMMARY					
Package	TO-247AC modified (2 pins)				
I _{F(AV)}	6 A				
V_{R}	1200 V				
V _F at I _F	2.4 V				
t _{rr} typ.	26 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA06PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Maximum continuous forward current	I _F	T _C = 100 °C	6			
Single pulse forward current	I _{FSM}		80	Α		
Maximum repetitive forward current	I _{FRM}		24			
Mayimum navar dissination	P _D	T _C = 25 °C	62.5	w		
Maximum power dissipation		T _C = 100 °C	25			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		



VS-HFA06PB120PbF, VS-HFA06PB120-N3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ	1200	-	-		
Maximum forward voltage		I _F = 6.0 A	-	2.7	3.0	V	
	V_{FM}	I _F = 12 A	-	3.5	3.9]	
		I _F = 6.0 A, T _J = 125 °C	-	2.4	2.8		
Maximum reverse		$V_R = V_R$ rated	-	0.26	5.0		
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	110	500	μA	
Junction capacitance	C _T	V _R = 200 V	-	9.0	14	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	$A/\mu s$, $V_R = 30 V$	-	26	-	ns	
Reverse recovery time	t _{rr1}	T _J = 25 °C	I _F = 6.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	53	80		
	t _{rr2}	T _J = 125 °C		-	87	130		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	Α	
	I _{RRM2}	T _J = 125 °C		-	5.0	9.0		
Poverse receivent charge	Q _{rr1}	T _J = 25 °C		-	116	320	nC	
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	233	585		
Peak rate of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	180	-		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	100	-	- A/μs	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	2.0			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount		-	80	K/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Maight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-247AC modified	HFA06PB120					



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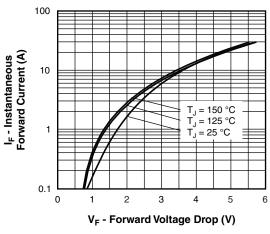


Fig. 1 - Typical Forward Voltage Drop Characteristics

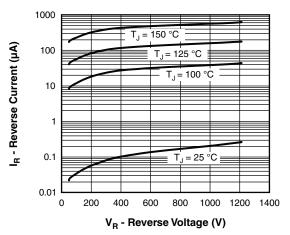


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

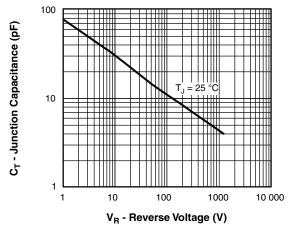


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

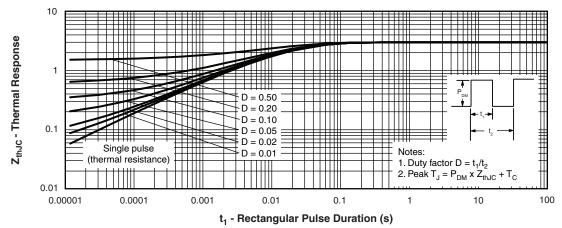


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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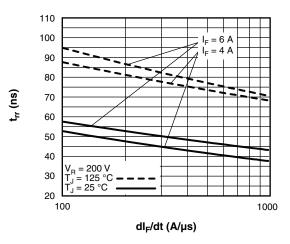
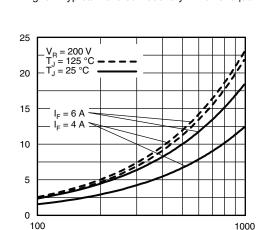


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt



 $dI_{F}/dt \ (A/\mu s)$ Fig. 6 - Typical Recovery Current vs. dI_{F}/dt

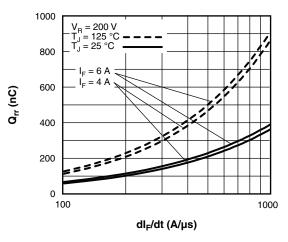


Fig. 7 - Typical Stored Charge vs. dl_F/dt

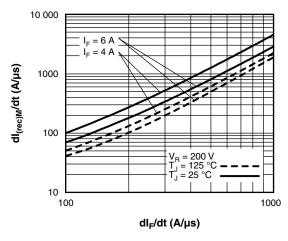


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

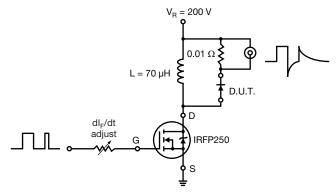
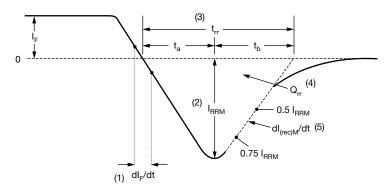


Fig. 9 - Reverse Recovery Parameter Test Circuit

I, **A**

VS-HFA06PB120PbF, VS-HFA06PB120-N3

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

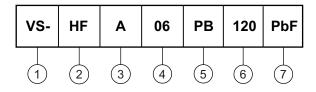
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 HEXFRED[®] family
- 3 Electron irradiated
- Current rating (06 = 6A)
- 5 PB = TO-247AC modified
- Voltage rating: (120 = 1200 V)
- 7 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA06PB120PbF	25	500	Antistatic plastic tube				
VS-HFA06PB120-N3	25	500	Antistatic plastic tube				

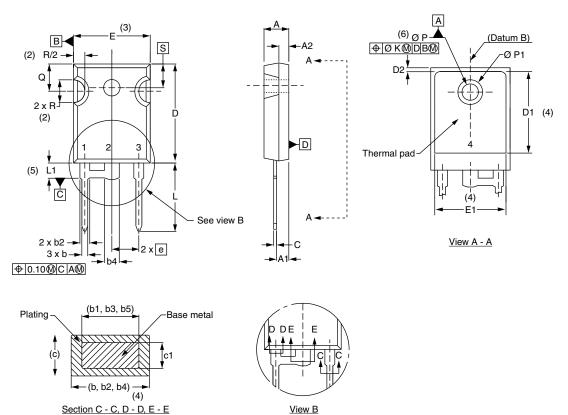
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95541</u>					
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255			
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442			



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DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	MILLIMETERS		INCHES		
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D2	0.51	1.30	0.020	0.051		
Е	15.29	15.87	0.602	0.625	3	
E1	13.72	=.	0.540	-		
е	5.46	BSC	0.215	BSC		
ØK	2.54		0.010			
L	14.20	16.10	0.559	0.634		
L1	3.71	4.29	0.146	0.169		
ØΡ	3.56	3.66	0.14	0.144		
Ø P1	-	6.98	-	0.275		
Q	5.31	5.69	0.209	0.224		
R	4.52	5.49	0.178	0.216		
S	5.51 BSC		0.217 BSC			
	•		•			

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c

Legal Disclaimer Notice



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